

BCW65ALT1G, BCW65CLT1G

General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	32	Vdc
Collector – Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

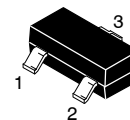
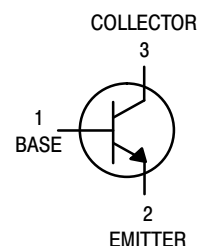
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



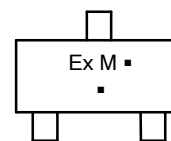
ON Semiconductor®

<http://onsemi.com>



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAMS



Ex = Device Code
x = A or C
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW65ALT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BCW65CLT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW65ALT1G, BCW65CLT1G

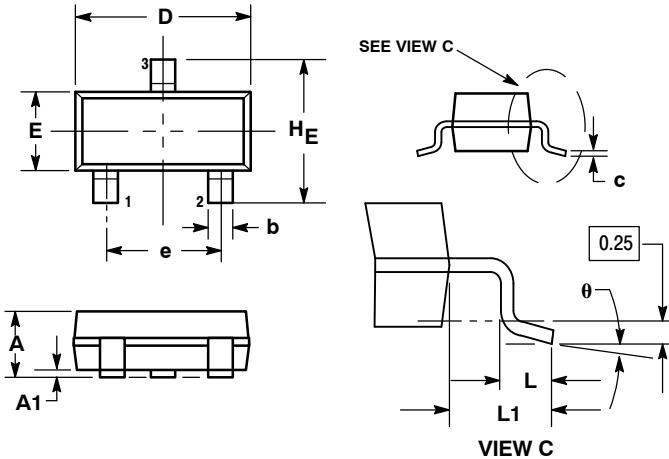
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	32	–	–	V _{dc}
Collector – Emitter Breakdown Voltage (I _C = 10 μA _{dc} , V _{EB} = 0)	V _{(BR)CES}	60	–	–	V _{dc}
Emitter – Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	5.0	–	–	V _{dc}
Collector Cutoff Current (V _{CE} = 32 V _{dc} , I _E = 0) (V _{CE} = 32 V _{dc} , I _E = 0, T _A = 150°C)	I _{CES}	–	–	20	nA _{dc} μA _{dc}
Emitter Cutoff Current (V _{EB} = 4.0 V _{dc} , I _C = 0)	I _{EBO}	–	–	20	nA _{dc}
ON CHARACTERISTICS					
DC Current Gain (I _C = 100 μA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 100 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 500 mA _{dc} , V _{CE} = 2.0 V _{dc})	BCW65ALT1 h _{FE}	35 75 100 35	– – – –	– – 250 –	–
DC Current Gain (I _C = 100 μA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 100 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 500 mA _{dc} , V _{CE} = 2.0 V _{dc})	BCW65CLT1 h _{FE}	80 180 250 100	– – – –	– – 630 –	–
Collector – Emitter Saturation Voltage (I _C = 500 mA _{dc} , I _B = 50 mA _{dc}) (I _C = 100 mA _{dc} , I _B = 10 mA _{dc})	V _{CE(sat)}	– –	0.7 0.3	– –	V _{dc}
Base – Emitter Saturation Voltage (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{BE(sat)}	–	–	2.0	V _{dc}
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain — Bandwidth Product (I _C = 20 mA _{dc} , V _{CE} = 10 V _{dc} , f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	–	12	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	–	–	80	pF
Noise Figure (V _{CE} = 5.0 V _{dc} , I _C = 0.2 mA _{dc} , R _S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB
SWITCHING CHARACTERISTICS					
Turn-On Time (I _{B1} = I _{B2} = 15 mA _{dc})	t _{on}	–	–	100	ns
Turn-Off Time (I _C = 150 mA _{dc} , R _L = 150 Ω)	t _{off}	–	–	400	ns

BCW65ALT1G, BCW65CLT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

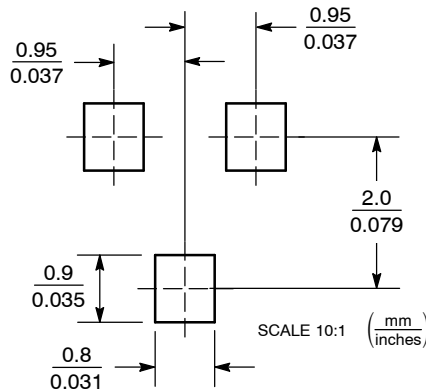
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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